



US1A THRU US1M

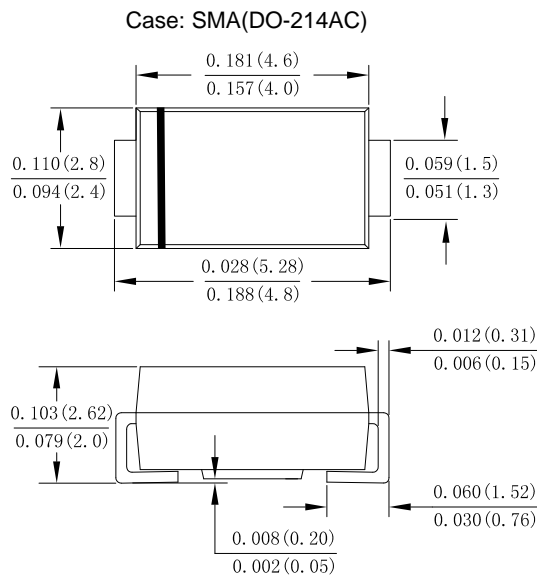
1.0AMP Ultra Fast Recovery Silicon Rectifier

Features

- Low Power Loss, High Efficiency
- Ideally Suited for Automatic Assembly
- Guard Ring Die Construction
- Plastic Case Material has UL Flammability Classification Rating 94V-0

Mechanical Data

- Case: Molded plastic SMA
- Terminals: Plated leads solderable per MIL-STD-750, Method 2026 guaranteed
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Marking: Type Number



Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified
Single phase, half wave, 60Hz, resistive or inductive load
For capacitive load derate current by 20%

Type Number	SYMBOL	US1A	US1B	US1D	US1G	US1J	US1K	US1M	Unit
Maximum Recurrent Peak Reverse Voltage	V _{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V _{DC}	50	100	200	400	600	800	1000	V
Average Rectified Output Current @T _L =100℃	I _F (AV)	1.0							A
Non-Repetitive Peak Forward Surge @T _j =25 ℃ Current 8.3ms Single half sine-wave@T _j =125 ℃ Superimposed On Rated Load (JEDEC Method)	I _{FSM}	30 24							A
Non-Repetitive Peak Forward Surge @T _j =25 ℃ Current 1.0ms Single half sine-wave @T _j =125℃ Superimposed On Rated Load (JEDEC Method)	I _{FSM}	60 48							A
10000 times of the wave surge current (time width 1ms, time interval 3s)	I _{FSM}	22.5							A
Rating for fusing (t<8.3ms)	I ² t	3.74							A ² s
Forward Voltage @IF=1.0A	V _{FM}	1.0			1.3	1.7			V
Peak Reverse Current @T _A =25 ℃	I _R	5.0					uA		
At Rated DC Blocking Voltage @T _A =125 ℃		200							
Maximum Reverse Recovery Time (Note 1)	T _{rr}	50				75			ns
Typical Junction Capacitance (Note 2)	C _J	8							pF
Typical Thermal Resistance	R _θ JL	27							℃/W
	R _θ JA	70							
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to+150							℃

Note: 1. Reverse Recovery Test Conditions: $I_F = 0.5A$, $I_R = 1.0A$, $IRR = 0.25A$.
2. Measured at 1.0 MHz and Applied reverse Voltage of 4.0V D.C



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Fig. 1 Forward Current Derating Curve

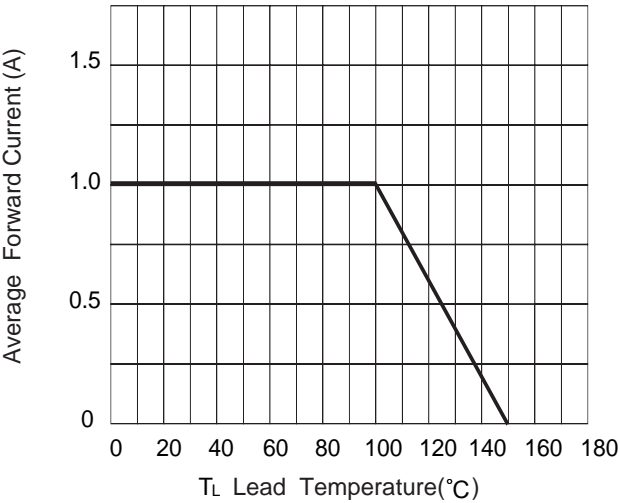


Fig. 2 Typ. Forward Characteristics

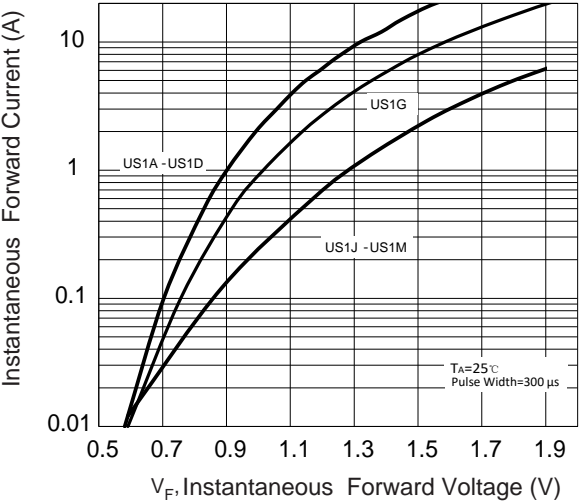


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

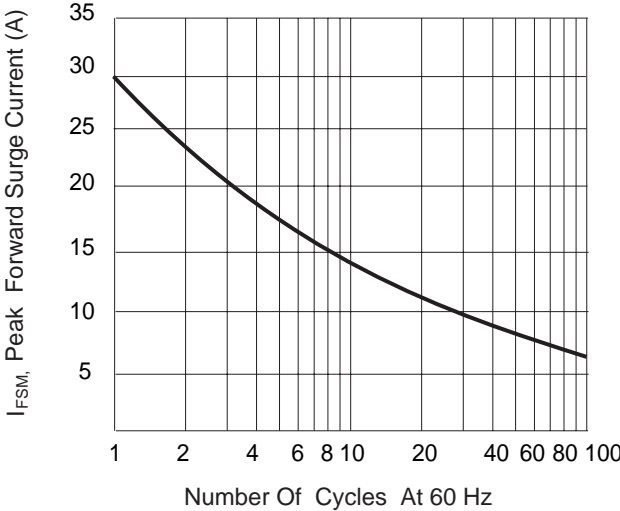


Fig.4 Typical Junction Capacitance

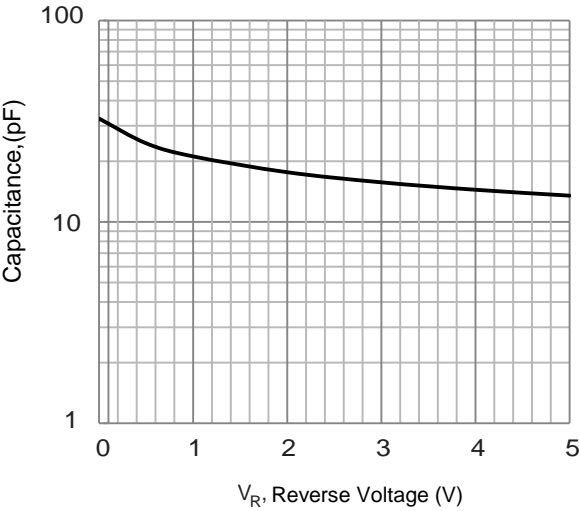


Fig.5 Typical Reverse Characteristics

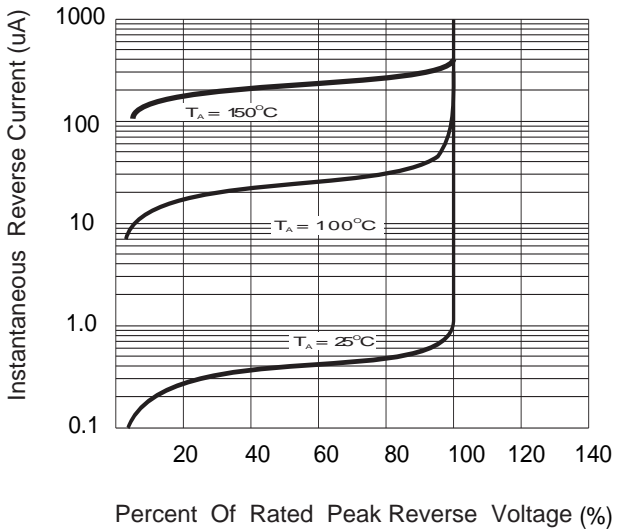
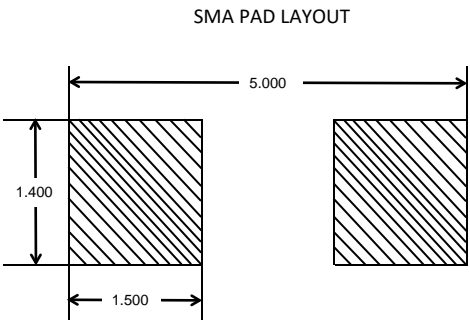


Fig.6 Mounting PAD Layout





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